

## N-Channel 80 V (D-S) Super Trench Power MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	80
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.006
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 6 V	0.0075
I <sub>D</sub> (A)	16
Configuration	Single

### FEATURES

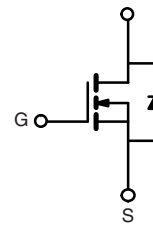
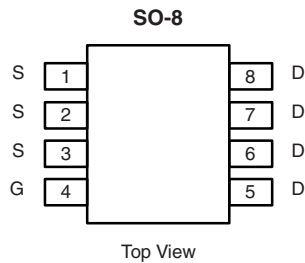
- Super Trench technology Power MOSFET
- Excellent gate charge x R<sub>ds (on)</sub> product(FOM)
- Very low on-resistance R<sub>ds (on)</sub>
- 100 % R<sub>g</sub> and UIS Tested



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- DC/DC Converter
- Ideal for hhigh-frequency swtitching and synchronous



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	80	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> = 25 °C	16	A
		T <sub>C</sub> = 125 °C	9	
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	6		
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	67		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	50	
Single Pulse Avalanche Energy		E <sub>AS</sub>	125	
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	7.1	W
		T <sub>C</sub> = 125 °C	2.3	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	80	°C/W
Junction-to-Foot (Drain)		R <sub>thJF</sub>	21	

### Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

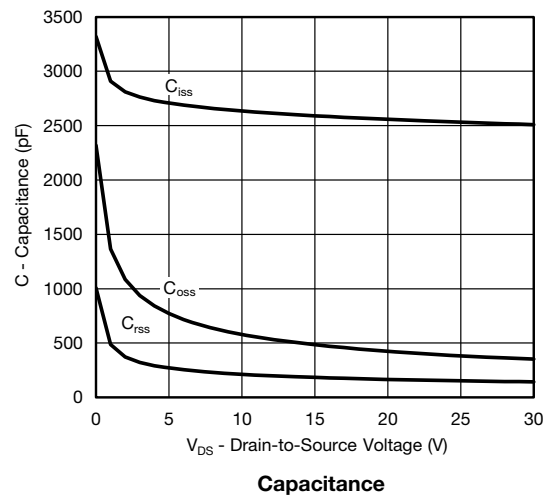
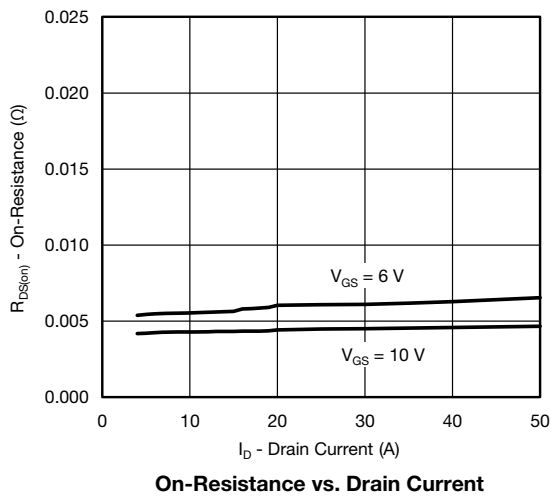
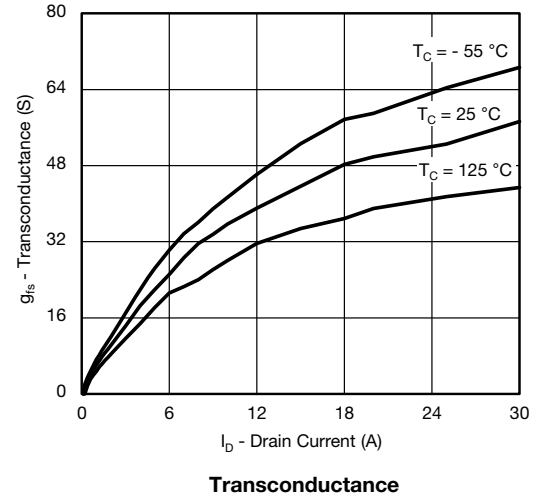
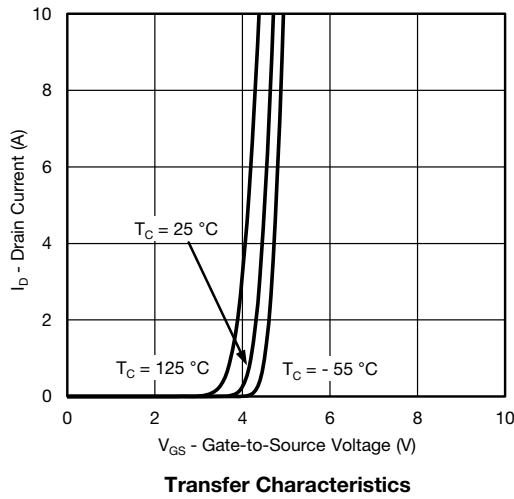
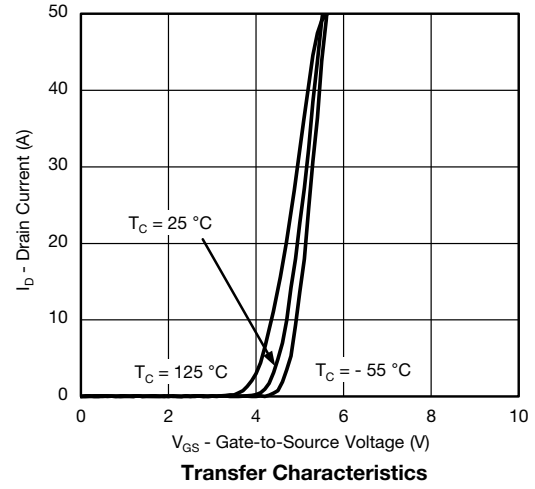
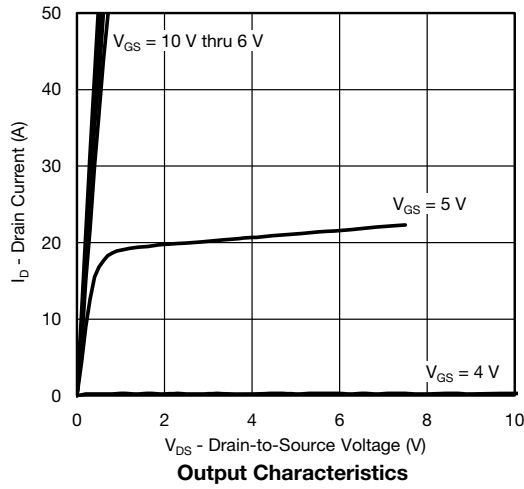
SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA		80	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.5	3.0	3.5	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1.0	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	30	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A	-	0.0048	-	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 125 °C	-	0.011	-	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 175 °C	-	0.015	-	
		V <sub>GS</sub> = 6 V	I <sub>D</sub> = 5 A	-	0.006	-	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 6 A		-	25	-	S
<b>Dynamic<sup>b</sup></b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V, f = 1 MHz	-	2531	3165	pF
Output Capacitance	C <sub>oss</sub>			-	382	480	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	153	195	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 12 A	-	45	68	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			-	9.9	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	11.2	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.40	0.87	1.30	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 2.5 Ω I <sub>D</sub> ≅ 12 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		-	13	20	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			-	12	18	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	25	38	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14	
<b>Source-Drain Diode Ratings and Characteristics<sup>b</sup></b>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	67	A
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.7 A, V <sub>GS</sub> = 0		-	0.72	1.2	V

**Notes**

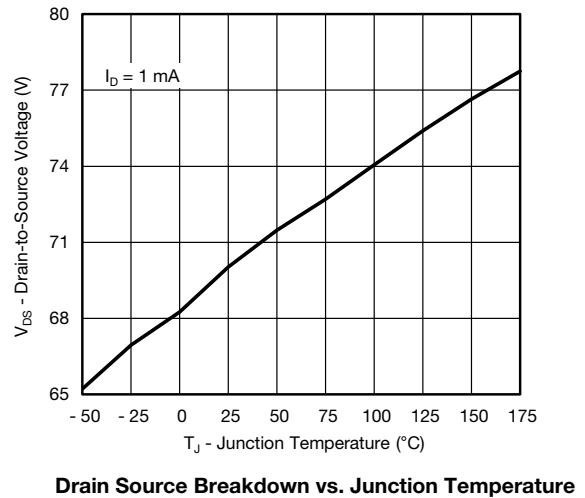
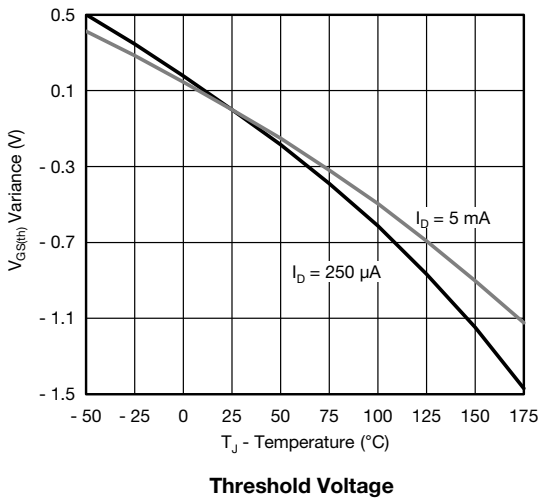
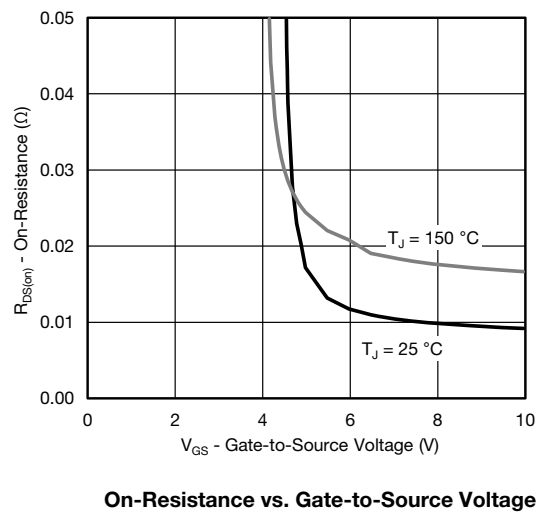
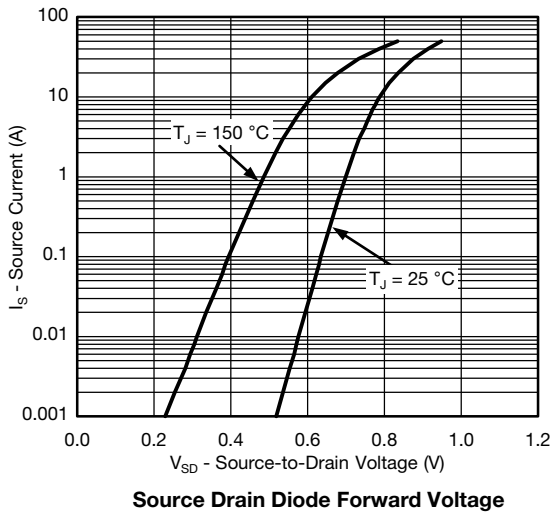
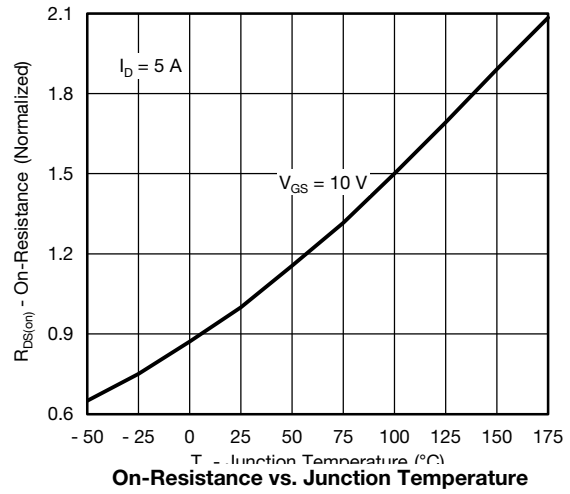
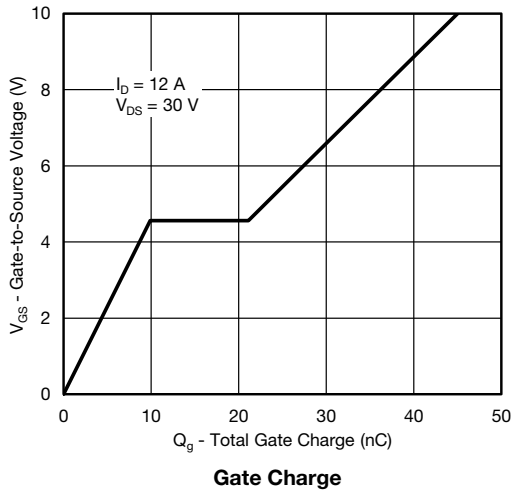
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

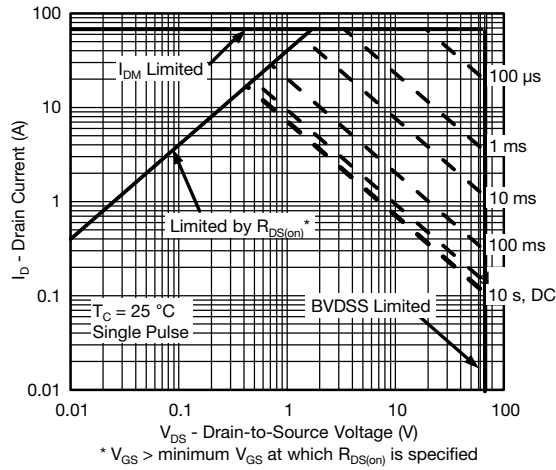
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



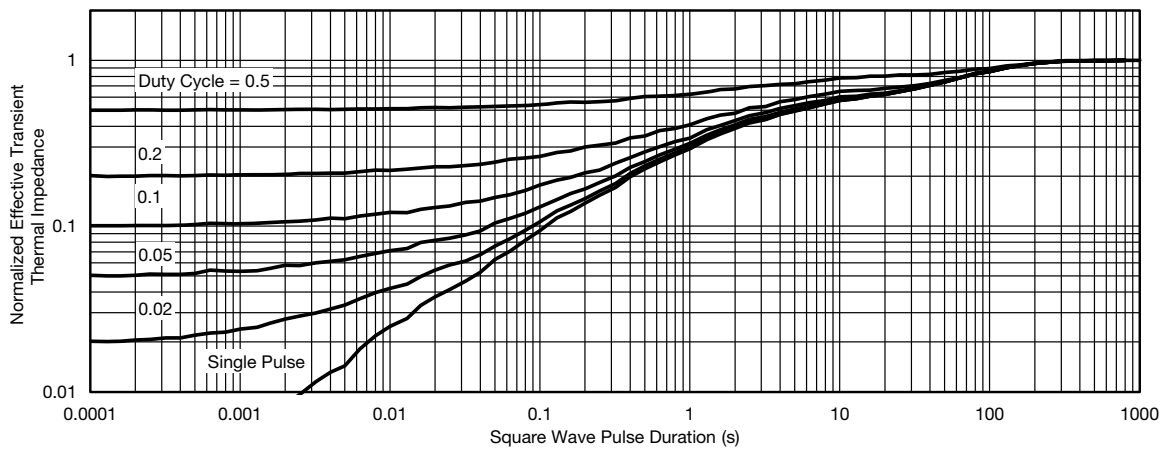
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

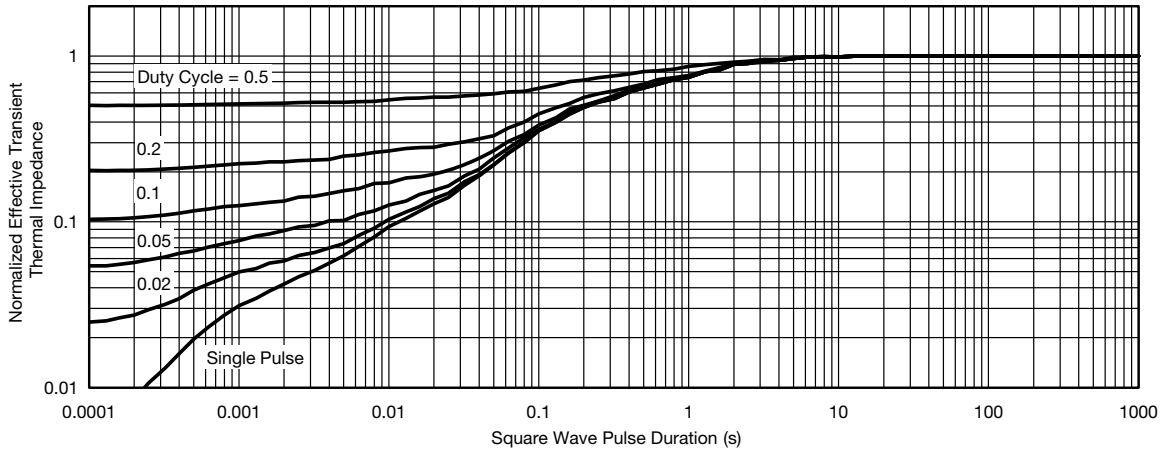


**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Foot**

**Note**

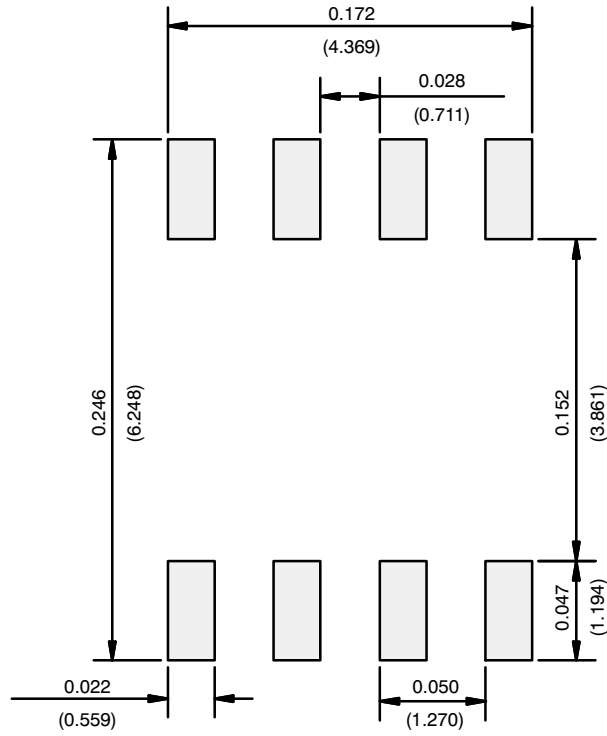
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Foot ( $25\text{ }^\circ\text{C}$ )
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulsed transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

**SOIC (NARROW): 8-LEAD**  
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)



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